

Année	Auteurs	Titre	Revue	Référence
2010	B. Bercu, L. Montès, F. Rochette, M. Mouis, X. Xin, P. Morfouli	Electron mobility increase in submicronic transistors integrated on ultra thin membranes subjected to high mechanical stress	Applied Physics Letters	Vol. 96, 092107:1-3 (March 2010)
2010	Yong Xu, T. Minari, K. Tsukagoshi, R. Gwoziecki, R. Coppard, F. Balestra, J.A. Chroboczek, G. Ghibaudo	Extraction of low-frequency noise in contact resistance of organic field-effect transistors	Applied Physics Letters	Vol. 97, 033503, 2010
2010	Yong Xu, R. Gwoziecki, I. Chartier, R. Coppard, F. Balestra, and G. Ghibaudo	Modified transmission-line method for contact resistance extraction in organic field-effect transistors	Applied Physics Letters	Vol. 97, 063302 (2010)
2010	Doyoung Jang, Jae Woo Lee, Kiichi Tachi, Laurent Montes, Thomas Ernst, Gyu Tae Kim and G. Ghibaudo	Low-frequency noise in strained SiGe core-shell nanowire p-channel field effect transistors	Applied Physics Letters	Vol. 97, 073505 (2010)
2010	Yong Xu, T. Minari, T. Kazuito, R. Gwoziecki, F. Balestra, J.A. Chroboczek, G. Ghibaudo	Diagnosis of low-frequency noise sources in contact resistance of staggered organic transistors	Applied Physics Letters	Vol. 98, 033505, 2011
2010	N. Rodriguez, F. Gamiz, S. Cristoloveanu	A-RAM memory cell : concept and operation	IEEE Electron Device Letters	Vol. 31, n° 9, 972-974 (2010)
2010	M. Charbonnier, C. Leroux, V. Cosnier, P. Besson, E. Martinez, N. Benedetto, C. Licitra, N. Rochat, C. Gaumer, K. Kaja, G. Ghibaudo, F. Martin, G. Reibold	Measurement of Dipoles/Roll-Off /Work functions by coupling CV and IPE and study of their dependence on fabrication process	IEEE Trans. Electron Devices	Vol. 57, 1819-1819 (2010)
2010	S. Puget, G. Bossu, P. Masson, P. Mazoyer, R. Ranica, A. Villaret, P. Lorenzini, J-M. Portal, D. Rideau, G. Ghibaudo, R. Bouchakour, G. Jacquemod, and T. Skotnicki	Modeling the Independent Double Gate Transistor in Accumulation Regime for 1TDRAM Application	IEEE Trans. Electron Devices	Vol. 57, 855-865 (2010)
2010	S. Cristoloveanu, N. Rodriguez, F. Gamiz	Why the universal mobility is not	IEEE Trans. Electron Devices	Vol. 57, n° 6, 1327-1333 (2010)
2010	K. Rogdakis, E. Bano, L. Montes, M. Bechelany, D. Cornu, K. Zekentes	Rectifying source and drain contacts for effective carrier transport modulation of extremely doped SiC nanowire FETs	IEEE Trans. Nanotechnology	Vol. 55, n°8, pp. 1970-1976 (Aug. 2008)
2010	E.X. Zhang, D.M. Fleetwood, F.E. Mamouni, M.L. Alles, R.D. Schrimpf, W. Xiong, C. Hobbs, K. Akarvardar, S. Cristoloveanu	Total ionizing dose effects on FinFET-based capacitor-less 1T-DRAMs	IEEE Trans. Nuclear Science	Vol. XX, n° XX, XX-XX (2010)
2010	Pascal Febvre, Torsten Reich	Superconductive Digital Magnetometers with Single-Flux-Quantum Electronics	IEICE	Vol.E93-C, n°4, pp. 445-452, Apr. 2010
2010	E. Nowak, E. Vianello, L. Perniola, M. Bocquet, G. Molas, R. Kies, M. Gely, G. Ghibaudo, B. De Salvo, G. Reibold, and F. Boulanger	Charge Localization during Program and Retention in Nitrided Read Only Memory-Like Nonvolatile Memory Devices	Japanese Journal of Applied Physics	Vol. 49, 04DD12 (2010).
2010	J.W. Lee, D. Jang, G. T. Kim, M. Mouis, G. Ghibaudo	Analysis of charge sensitivity and low frequency noise limitation in silicon nanowire sensors	Journ. Appl. Phys.	Vol. 107, 044501 (2010)
2010	Pascal Febvre, David Bouis, Natascia De Leo, Matteo Fretto, Andrea Soso, Vincenzo Lacquaniti	Electrical parameters of niobium-based overdamped superconductor - normal metal - insulator-superconductor Josephson junctions for digital applications	Journ. Appl. Phys.	Vol. 107, 103927, 2010.

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2010	Yong Xu, Takeo Minari, Kazuhito Tsukagoshi, J. A. Chroboczek and G. Ghibaudo	Direct evaluation of low-field mobility and access resistance in pentacene field-effect transistors	Journ. Appl. Phys.	Vol. 107, 114507 (2010)
2010	E. G. Ioannidis, C. G. Theodorou, A. Tsormpatzoglou, D. H. Tassis, K. Papatthanasidou, C. A. Dimitriadis, J. Jomaah, and G. Ghibaudo,	Analytical low-frequency noise model in the linear region of lightly doped nanoscale double-gate metal-oxide-semiconductor field-effect transistors	Journ. Appl. Phys.	Vol. 108, 064512 (2010)
2010	G. Gomard, E. Drouard, X. Letartre, X. Meng, A. Kaminski, A. Fave, M. Lemiti, E. Garcia-Caure and C. Seassal	Two-dimensional photonic crystal for absorption enhancement in hydrogenated amorphous silicon thin film solar cells	Journ. Appl. Phys.	Vol. 108, 123102 (2010)
2010	F. Domengie, J.L. Regolini, and D. Bauza	Study of Metal Contamination in CMOS Image Sensors by Dark-Current and Deep-Level Transient Spectroscopies	Journal of Electronic Materials	Vol. 39, n°6, 625-629 (2010)
2010	L. Pham-Nguyen, C. Fenouillet-Beranger, P. Perreau, S. Denorme, G. Ghibaudo, O. Faynot, T. Skotnicki, A. Ohata, M. Casse, M. Bawedin, W. Vand den Daele, K-H. Park, S-J. Chang, Y-H. Bae, I. Ionica, S. Cristoloveanu	Advanced Solutions For Mobility Enhancement in SOI MOSFETs	Journal of High Speed Electronics, in press (2010).	In press
2010	C. Boulord, A. Kaminski, B. Canut, S. Cardinal, M. Lemiti	Electrical and structural characterization of electroless nickel-phosphorous contacts for silicon solar cells metallization	Journal of the Electrochemical Society	Vol. 157 H742 (2010)
2010	A. Tsormpatzoglou, D. H. Tassis, C. A. Dimitriadis, G. Ghibaudo, G. Pananakakis, N. Collaert	Analytical modeling for the current-voltage characteristics of lightly-doped symmetric double-gate MOSFETs	Microelectronic Engineering	Vol. 87, 1764-1768 (2010)
2010	D.H. Tassis, A. Tsormpatzoglou, C.A. Dimitriadis, G. Ghibaudo, G. Pananakakis, N. Collaert	Source/drain optimization of underlapped lightly doped nanoscale double gate MOSFETs	Microelectronic Engineering	Vol. 87, 23534-2357 (2010)
2010	L. Gerrer, M. Rafik, G. Ribes, G. Ghibaudo and E. Vincent,	Unified soft breakdown MOSFETs compact model: From experiments to circuit simulation	Microelectronics Reliability	Vol. 50, 1259-1262 (2010)
2010	B. Hackens, F. Martins, S. Faniel, C. A. Dutu, H. Sellier, S. Huant, M. Pala, L. Desplanque, X. Wallart, V. Bayot	Imaging Coulomb Islands in a Quantum Hall Interferometer	Nature Communications	Vol. 1, p. 39 (2010)
2010	S. Anders, M. Blamire, F.-Im. Buchholz, D.-G. Crété, R. Cristiano, P. Febvre, L. Fritzsche, A. Herr, E. Il'ichev, J. Kohlmann, J. Kunert, H.-G. Meyer, J. Niemeyer, T. Ortlev, H. Rogalla, T. Schurig, M. Siegel, R. Stolz, E. Tarte, M. Ter Brake, H. Töpfer, J.-C. Villegier, A.M. Zagorskin, A.B. Zorin	European roadmap on superconductor electronics: status and perspectives	Physica C	Vol. 470, Issues 23-24, pp. 2079-2126, Dec. 2010; doi:10.1016/j.physc.2010.07.005
2010	D. J. Eldridge, M. G. Pala, M. Governale, J. König	Superconducting proximity effect in interacting double-dot systems	Physical Review B	Vol. 82, p. 184507 (2010)
2010	S. Estevez Hernandez, M. Akabori, K. Sladek, Ch. Volk, S. Alagha, H. Hardtdegen, M.G. Pala, N. Demarina, D. Grützmacher, Th. Schäpers	Spin-orbit coupling and phase-coherence in InAs nanowires	Physical Review B	Vol. 82, p. 235303 (2010)
2010	J-M. Hartmann, L. Sanchez, W. Van Den Daele, A. Abadie, L. Baud, R. Truche, E. Augendre, L. Clavelier, N. Cherkashin, M. Hytch, S. Cristoloveanu	Fabrication, structural and electrical properties of compressively strained Ge-on-insulator substrates.	Semicond. Sci. Technol.	Vol. 25, n° 7, 075010 (2010)

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2010	A. Braggio, M. G. Pala, M. Governale, J. König	Superconducting proximity effect in interacting quantum dots revealed by shot noise	Solid State Communications	Vol. 151, p. 155 (2011)
2010	Yong Xu, Takeo Minari, Kazuhito Tsukagoshi, Jan Chroboczek, Francis Balestra, G. Ghibaudo	Origin of low-frequency noise in pentacene field-effect transistors	Solid State Electronics	In Press, Corrected Proof, Available online 4 February 2011
2010	C. M. Mezzomo, A. Bajolet, A. Cathignol, E. Josse and G. Ghibaudo	Modeling Local Electrical Fluctuations in 45nm Heavily Pocket-implanted Bulk MOSFET	Solid State Electronics	Vol. 54, 1359–1366 (2010)
2010	M. Bawedin, S. Cristoloveanu, D. Flandre, F. Udrea	Dynamic body potential variation in FD SOI MOSFETs operated in deep non-equilibrium regime : model and applications	Solid State Electronics	Vol. 54, n° 2, pp. 104-114 (Feb. 2010)
2010	L. Pham-Nguyen, C. Fenouillet-Beranger, G. Ghibaudo, T. Skotnicki, S. Cristoloveanu	Mobility enhancement by CESL strain in short-channel ultrathin SOI MOSFETs	Solid State Electronics	Vol. 54, n° 2, pp. 123-130 (Feb. 2010)
2010	W. Van Den Daele, E. Augendre, C. Le Royer, J-F. Damlencourt, B. Grandchamp, S. Cristoloveanu	Low-temperature characterization and modeling of advanced GeOI pMOSFETs : mobility mechanism and origin of the parasitic conduction	Solid State Electronics	Vol. 54, n° 2, pp. 205-212 (2010)
2010	E.X. Zhang, D.M. Fleetwood, M.L. Alles, R.D. Schrimpf, F.E. Mamouni, W. Xiong, S. Cristoloveanu	Effects of fin width on memory windows in FinFET ZRAMs.	Solid State Electronics	Vol. 54, n°10, pp. 1155-1159 (Oct. 2010)
2010	A. Zaka, Q. Raffay, M. Iellina, P. Palestri, R. Clerc, D. Rideau, D. Garetto, E. Dornel, J. Singer, C. Tavernier, G. Pananakakis, H. Jaouen	On the Accuracy of Current TCAD Hot Carrier Injection Models in Nanoscale Devices	Solid State Electronics	Vol. 54, n°12, 1669-1674 (Dec. 2010)
2010	M. Ferrier, D. Zhang, P. Griffin, R. Clerc, S. Monfray, T. Skotnicki, Yoshio Nishi	Performance and analytical modeling of Metal-Insulator-Metal Field Controlled Tunnel Transistors	Solid State Electronics	Vol. 54, n°12, pp. 1525-1531 (Dec. 2010)
2010	J. Antoszewski, J.M. Dell, L. Faraone, N. Bresson, S. Cristoloveanu	Electron magnetoresistance mobility in silicon-on-insulator layers using Kelvin's technique	Solid State Electronics	Vol. 54, n°9, 1047-1050 (2010)
2010	J. Coignus, C. Leroux, R. Clerc, R. Truche, G. Ghibaudo, G. Reibold and F. Boulanger	HfO2-based Gate Stacks Transport Mechanisms and Parameter Extraction	Solid State Electronics	Vol. 54, n°9, 972-978 (Sept. 2010)
2010	J.L. Huguenin, G. Bidal, S. Denorme, D. Fleury, N. Loubet, A. Pouydebasque, P. Perreau, F. Leverd, S. Barnola, R. Beneyton, B. Orlando, P. Gouraud, T. Salvetat, L. Clement, S. Monfray, G. Ghibaudo, F. Boeuf and T. Skotnicki	Gate-all-around technology: Taking advantage of ballistic transport?	Solid State Electronics	Vol. 54, n°9, pp. 883-889 (Sept. 2010)